

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A semiconductor laser device, comprising:
an insulative frame;
a semiconductor laser element disposed inside the insulative frame, the semiconductor laser element emitting laser light in a plane direction;
a reflection mirror disposed inside the insulative frame, the reflection mirror reflecting the laser light in an upper direction;
a light acceptance unit for signal detecting disposed inside the insulative frame, the light acceptance unit detecting signal signals of incident laser light; and
a plurality of leads fixed in the end walls opposed to each other in the longitudinal direction of the insulative frame, the plurality of leads extending in a horizontal direction;
wherein the insulative frame is made of liquid crystal polymer, and
wherein one end of each of the leads protrudes inside the end walls and openings are formed above and beneath the end of each of the leads which protrudes inside the end walls on upper and lower surfaces of the insulative frame.

2. (Canceled)

3. (Original) A semiconductor laser device as in Claim 1, wherein thick portions are formed on both side walls extending in a longitudinal direction of the insulative frame.

4. (Original) A semiconductor laser device as in Claim 1, wherein the reflection mirror is mounted using UV resin.

5. (Original) A semiconductor laser device as in Claim 1, wherein the light acceptance unit for signal detecting comprises two light acceptance units.

6. (New) A semiconductor laser device, comprising:
an insulative frame;

a semiconductor laser element disposed inside the insulative frame, the semiconductor laser element emitting laser light in a plane direction;

a reflection mirror disposed inside the insulative frame, the reflection mirror reflecting the laser light in an upper direction;

a light acceptance unit for signal detecting disposed inside the insulative frame, the light acceptance unit detecting signals of incident laser light; and

a plurality of leads fixed in end walls opposed to each other in the longitudinal direction of the insulative frame, the plurality of leads extending outwardly in a horizontal direction,

wherein the insulative frame is made of liquid crystal polymer, and thick portions are formed on opposing side walls extending in a longitudinal direction of the insulative frame.

7. (New) A semiconductor laser device as in Claim 6, wherein the reflection mirror is mounted using UV resin.

8. (New) A semiconductor laser device as in Claim 6, wherein the light acceptance unit for signal detecting comprises two light acceptance units.